

FIG. 1

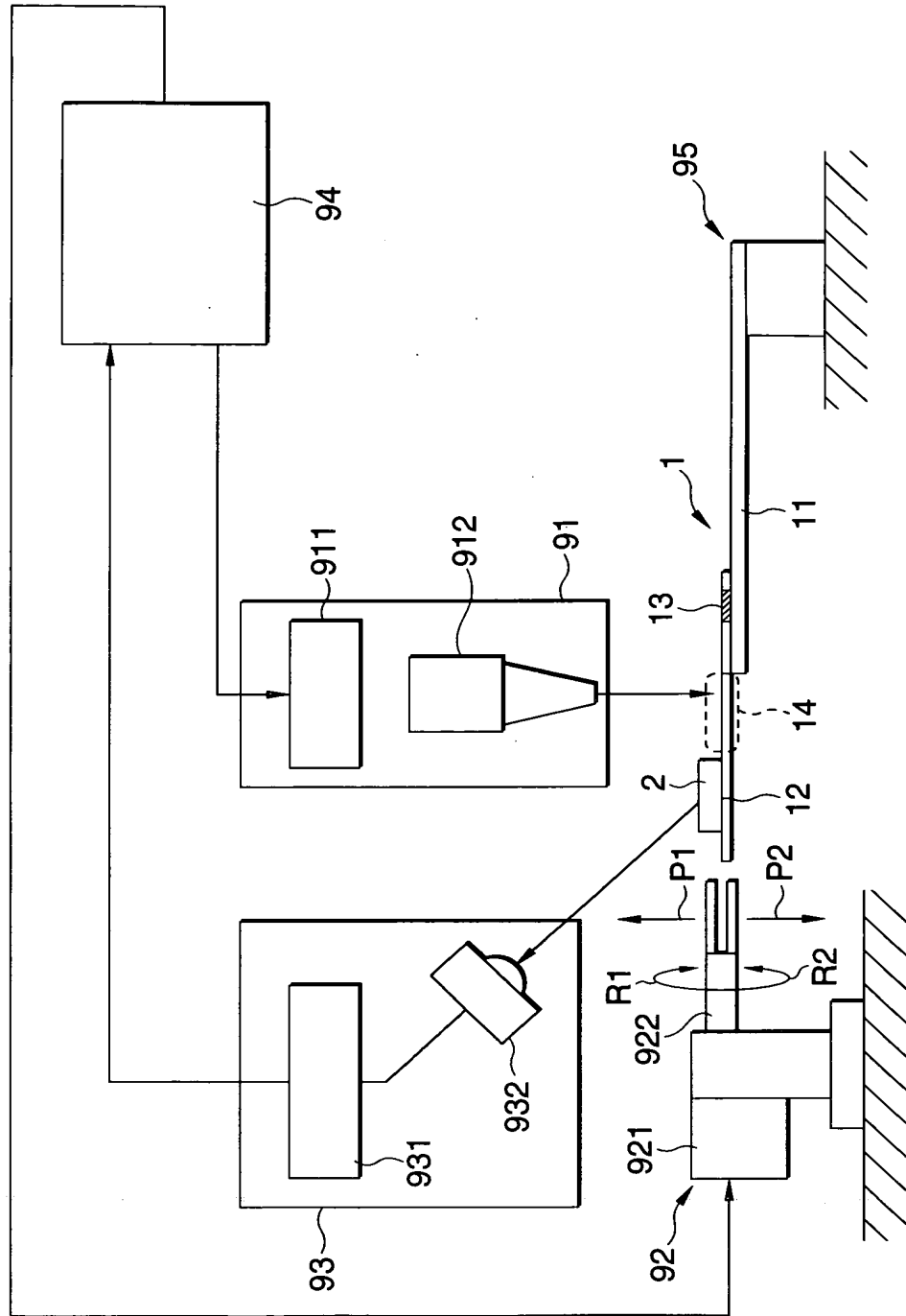
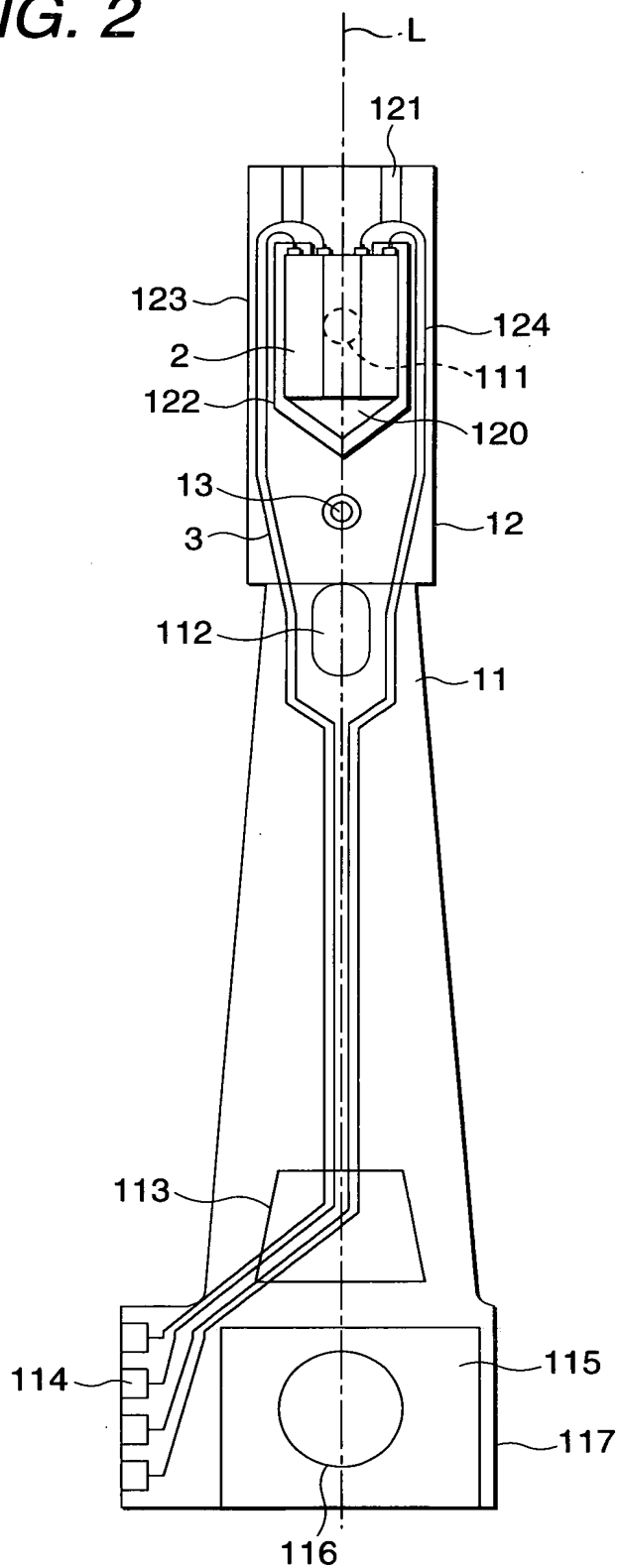
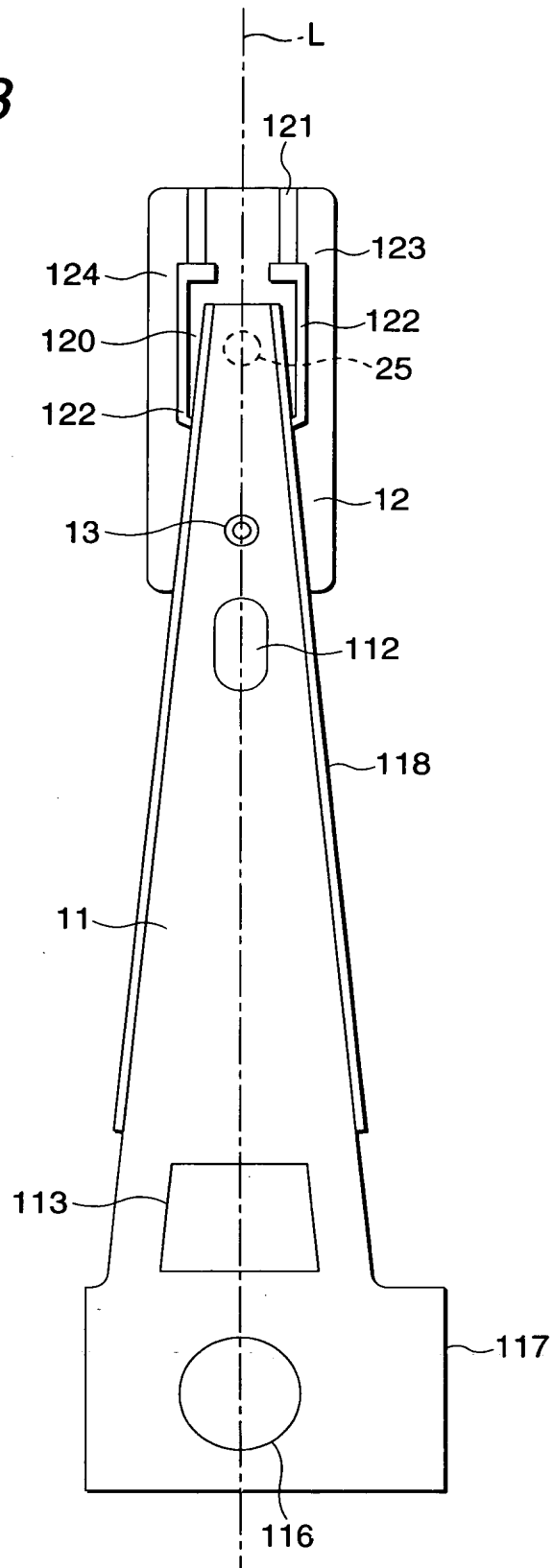


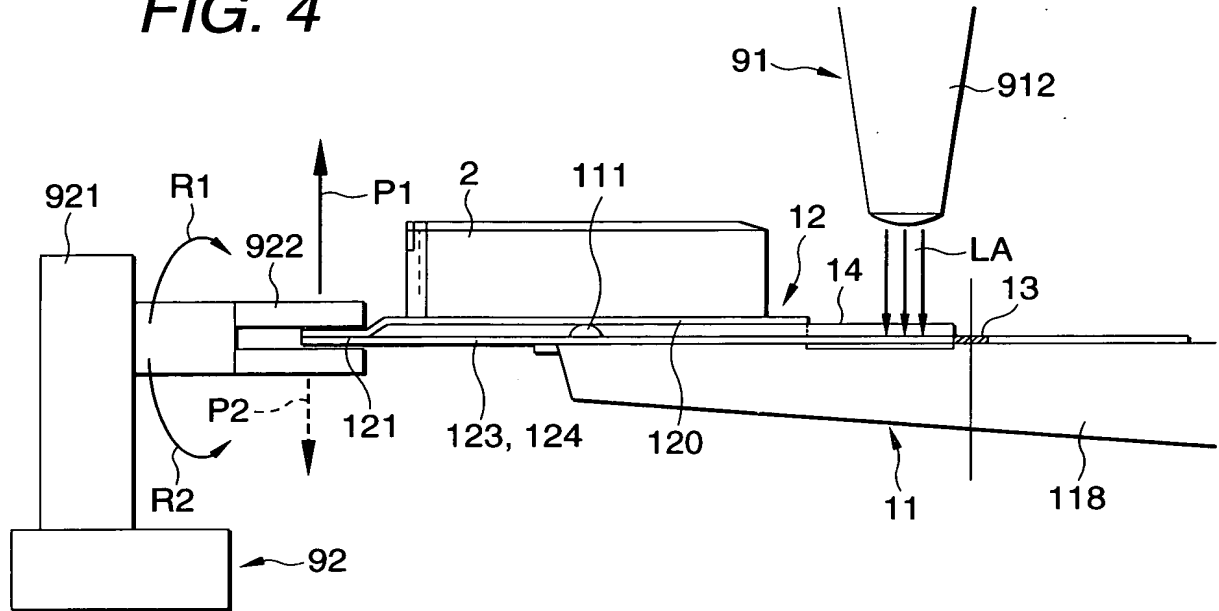
FIG. 2



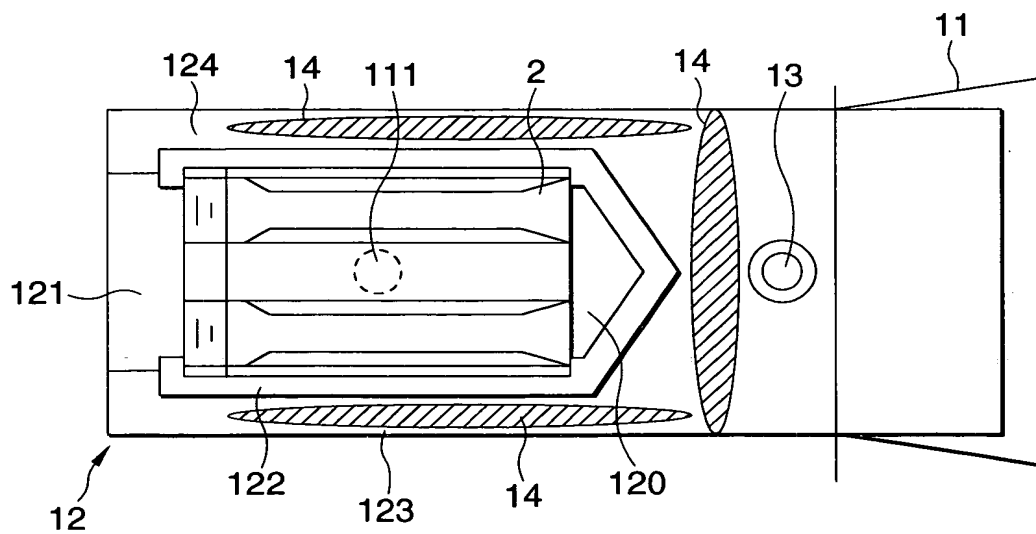
**FIG. 3**



**FIG. 4**



**FIG. 5**

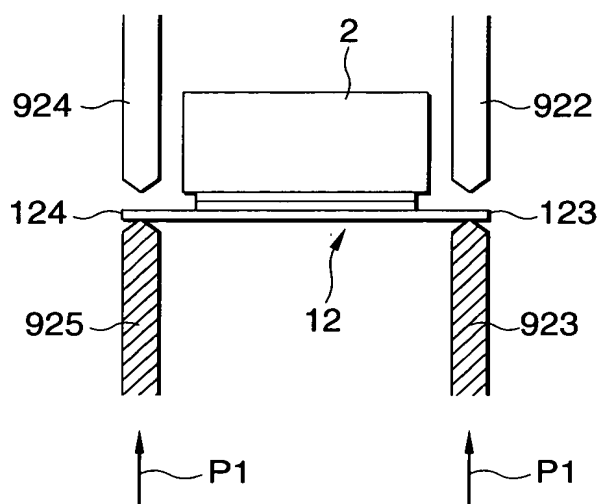


[illegible]

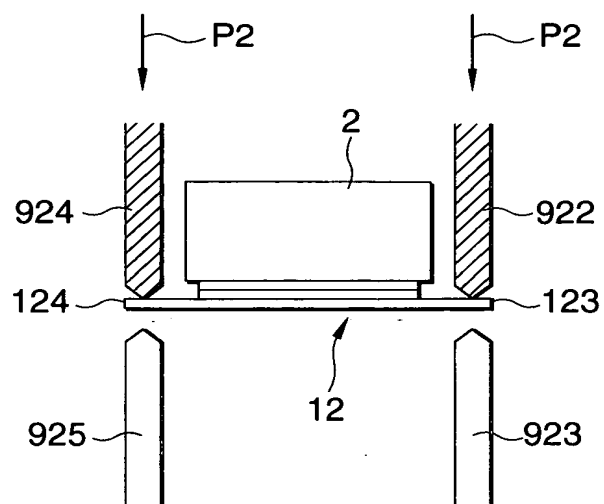
A cross-sectional diagram of a semiconductor device assembly. A substrate 118 is shown at the bottom right, sloping upwards to the left. On top of the substrate is a layer 11. A horizontal layer 120 is positioned above the substrate. Above layer 120 are two main rectangular blocks: block 2 on the right and block 121 on the left. Block 121 has a small protrusion 123 on its top surface. To the left of block 121 is another block 921. A vertical dashed arrow labeled P2 points downwards from the interface between block 121 and block 921. A curved arrow labeled R2 indicates a clockwise rotation around a point below block 121. To the right of block 2 is a thin layer 14. Above layer 14 is a vertical structure 12. A curved arrow labeled R1 indicates a counter-clockwise rotation around a point above block 121. An upward-pointing arrow labeled P1 is located above block 121. At the top right, a probe or needle 91 is shown with its tip touching the top surface of block 2. The probe has a handle 912 and a contact tip 911. Three downward arrows labeled LA indicate the contact area between the probe tip and block 2. Other labels include 922 pointing to the top of block 121, 111 pointing to the side of block 2, and 12 pointing to the vertical structure.



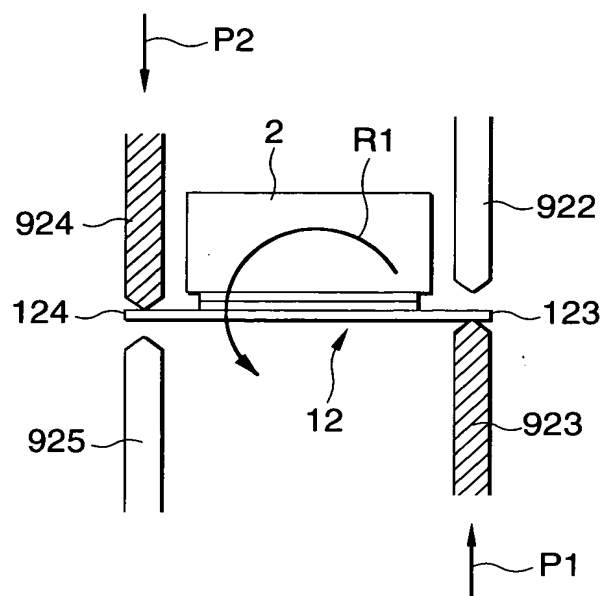
**FIG. 10**



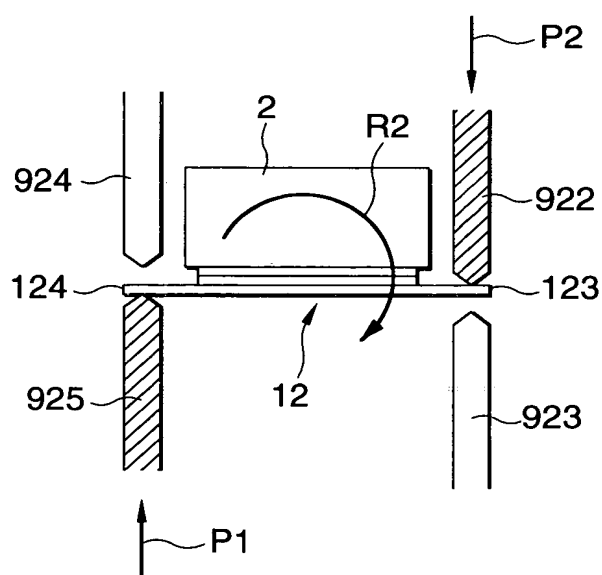
**FIG. 11**



**FIG. 12**

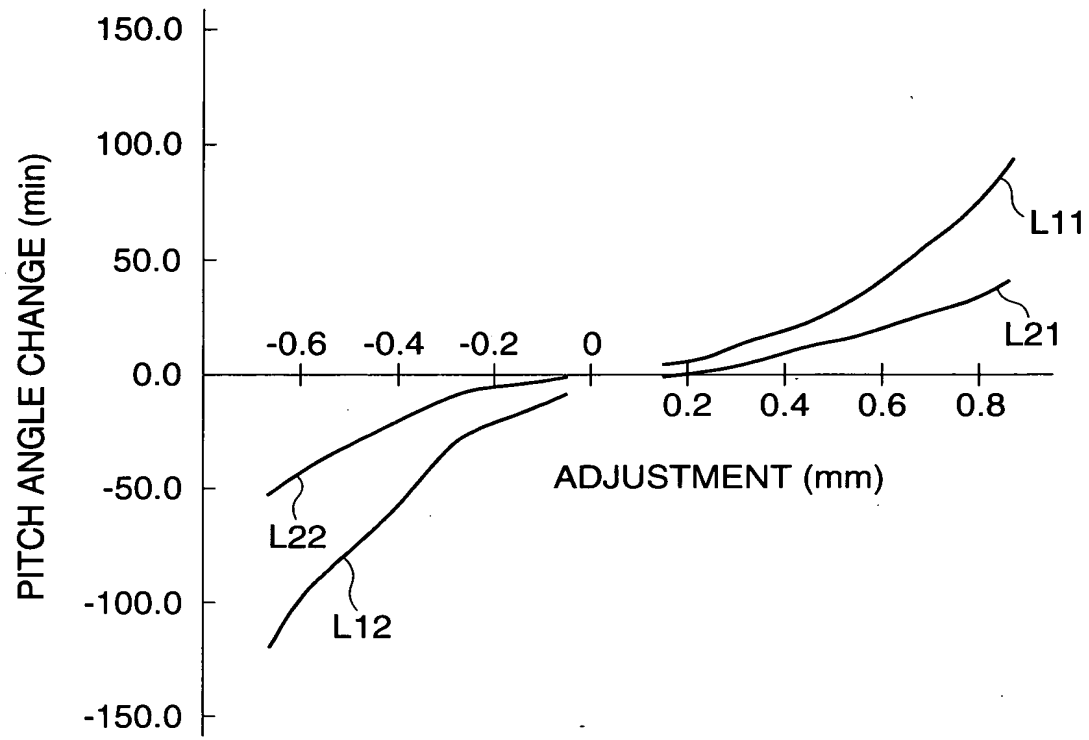


**FIG. 13**





**FIG. 14**



**FIG. 15**

